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## FDN5632N-F085

# N-Channel Logic Level PowerTrench<sup>®</sup> MOSFET 60 V, 1.6 A, 98 m $\Omega$

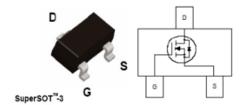
#### **Features**

- $\blacksquare$  R<sub>DS(on)</sub> = 98 m $\Omega$  at V<sub>GS</sub> = 4.5 V, I<sub>D</sub> = 1.6 A
- $\blacksquare$  R<sub>DS(on)</sub> = 82 m $\Omega$  at V<sub>GS</sub> = 10 V, I<sub>D</sub> = 1.7 A
- Typ  $Q_{g(TOT)}$  = 9.2 nC at  $V_{GS}$  = 10 V
- Low Miller Charge
- UIS Capability
- Qualified to AEC Q101
- RoHS Compliant

#### **Applications**

- DC/DC converter
- Motor Drives





### MOSFET Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain to Source Voltage	60	V
$V_{GS}$	Gate to Source Voltage	±20	V
1	Drain Current Continuous (V <sub>GS</sub> = 10V)	1.7	Α
I <sub>D</sub>	Pulsed	10	1 ^
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)	74	mJ
$P_D$	Power Dissipation	1.1	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature	-55 to +150	°C
$R_{\theta JC}$	Thermal Resistance Junction to Case	75	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient TO-252, 1in <sup>2</sup> copper pad area	111	°C/W

#### Note

1:  $E_{AS}$  of 74mJ is 100% test at L=80mH,  $I_{AS}$ =1.4A, starting  $T_{J}$  = 25  $^{\circ}C$ 

## **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
5632	FDN5632N-F085	SSOT3	7"	8mm	3000 units

## **Electrical Characteristics** $T_A = 25^{\circ}C$ unless otherwise noted

Parameter

On Ch	aracteristics						
B <sub>VDSS</sub>	Drain to Source Breakdown Voltage	I <sub>D</sub> = 250μA, V <sub>GS</sub> =	= 0V	60	-	-	V
I <sub>DSS</sub> Zero Gate Voltage Drain Curre	Zana Cata Valtana Duain Comment	V <sub>DS</sub> = 48V,		-	-	1	^
	Zero Gate voltage Drain Current	$V_{GS} = 0V$	$T_A = 125^{\circ}C$	-	-	250	μΑ
loss	Gate to Source Leakage Current	$V_{CC} = +20V$		-	_	+100	nA

**Test Conditions** 

Min

Max

Тур

Units

#### **On Characteristics**

Symbol

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1	2.0	3	V
		I <sub>D</sub> = 1.7A, V <sub>GS</sub> = 10V	-	57	82	
		I <sub>D</sub> = 1.6A, V <sub>GS</sub> = 6V	-	62	88	
r <sub>DS(on)</sub>		I <sub>D</sub> = 1.6A, V <sub>GS</sub> = 4.5V		70	98	mΩ
		I <sub>D</sub> = 1.7A, V <sub>GS</sub> = 10V, T <sub>A</sub> = 150°C	-	107	135	

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	$-V_{DS} = 15V$ , $V_{GS} = 0V$ , -f = 1MHz		-	475	-	pF
Coss	Output Capacitance			-	60	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			-	30	-	pF
$R_G$	Gate Resistance			-	1.4	-	Ω
$Q_{g(TOT)}$	Total Gate Charge at 10V	V <sub>GS</sub> = 0 to 10V	\/ - 20\/	-	9.2	12	nC
Q <sub>gs</sub>	Gate to Source Gate Charge	$V_{DD} = 20V$ $I_{D} = 1.7A$		-	1.5	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge			-	1.4	-	nC

## **Electrical Characteristics** $T_A = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units

## **Switching Characteristics**

t <sub>on</sub>	Turn-On Time		-	-	30	ns
t <sub>d(on)</sub>	Turn-On Delay Time	.,	-	15	-	ns
t <sub>r</sub>	Rise Time	$V_{DD} = 30V, I_{D} = 1.0A$ $V_{GS} = 10V, R_{GEN} = 6\Omega$	-	1.7	-	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 012	-	5.2	-	ns
t <sub>f</sub>	Fall Time		-	1.3	-	ns
t <sub>off</sub>	Turn-Off Time		-	-	12.9	ns

#### **Drain-Source Diode Characteristics**

V <sub>SD</sub>	Source to Drain Diode Voltage	I <sub>SD</sub> = 1.7A	-	0.8	1.25	V
		$I_{SD} = 0.85A$	-	0.8	1.0	
t <sub>rr</sub>	Reverse Recovery Time	I <sub>SD</sub> = 1.7A, dI <sub>SD</sub> /dt = 100A/μs	-	16.0	21	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	7.9	10.3	nC

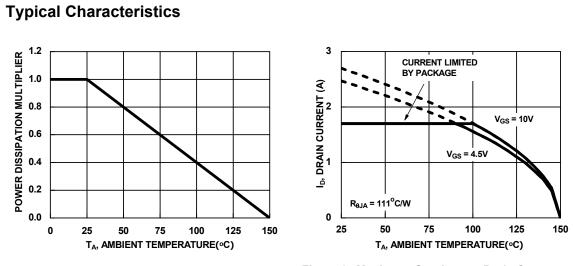


Figure 1. Normalized Power Dissipation vs. Case Temperature

Figure 2. Maximum Continuous Drain Current vs.

Case Temperature

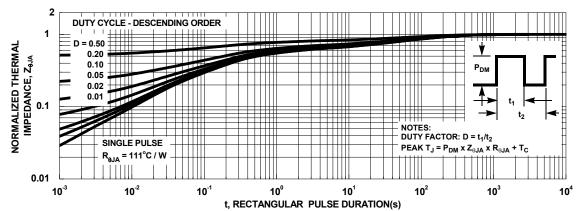


Figure 3. Normalized Maximum Transient Thermal Impedance

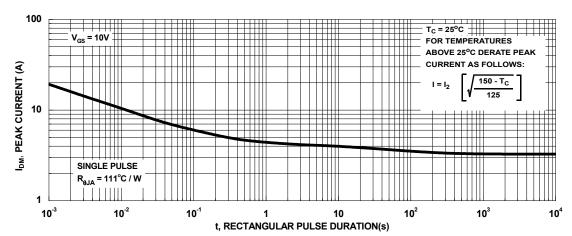


Figure 4. Peak Current Capability

#### **Typical Characteristics**

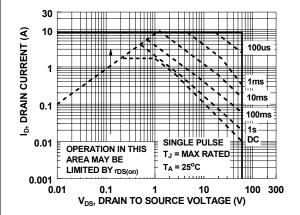
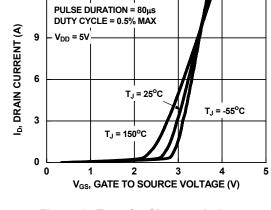


Figure 5. Forward Bias Safe Operating Area



12

Figure 6. Transfer Characteristics

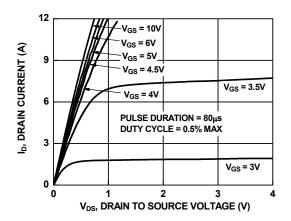


Figure 7. Saturation Characteristics

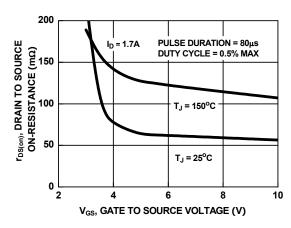


Figure 8. Drain to Source On-Resistance Variation vs Gate to Source Voltage

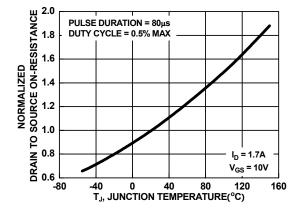


Figure 9. Normalized Drain to Source On Resistance vs Junction Temperature

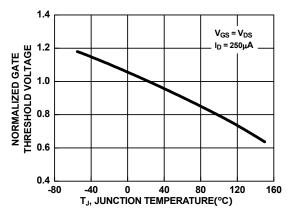


Figure 10. Normalized Gate Threshold Voltage vs Junction Temperature

## **Typical Characteristics**

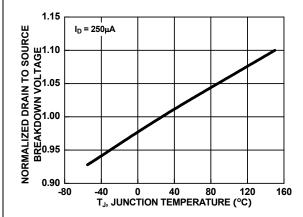


Figure 11. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

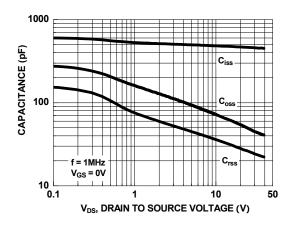


Figure 12. Capacitance vs Drain to Source Voltage

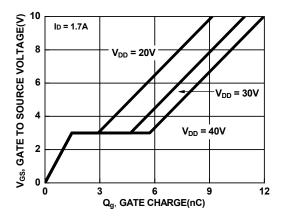


Figure 13. Gate Charge vs Gate to Source Voltage

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